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Magnetic Sensor ICs

Dual Outputs for both S and N-pole Low Power Hall-Effect Sensor IC

General Description

Using low power CMOS process, the AS1821 is designed for low power, high performance unipolar detection dual output hall-effect application, such as cover switch, contactless switch, solid state switch and lid close sensor etc battery operation. The hall IC integrated an on-chip hall voltage generator for magnetic sensing, a comparator that amplifiers the hall voltage, a chopper amplifier, a Schmitt trigger to provide switching hysteresis for noise rejection, and two complementary output.

The total power consumption of AS1821 is typically less than 1.7uA at 1.8V power supply. AS1821 is designed to respond to alternating North and South poles. White the magnetic flux density (B) is larger than operate point (B_{OP}), the output will be turned on (low), the output is held until the magnetic flux density (B) is lower than release point (B_{PP}), then turn off (high).

The device is available in SOT23-5L, DFN1014-4L and DFN1010-4L package is rated over the -40°C to 125°C. The all packages are RoHS and Green compliant.

Features

- Input Voltage Range : 1.65V to 5.0V
- Micro-power consumption ideal for battery power applications
- Uniplar Operation, dual output
- Very high sensitivity hall sensor
- Low Power CMOS process technology
- Chopper stabilization amplifier stage
- Magnetic Sensitivity (typical) B_{OPS}=40Gauss, B_{RPS}=20Gauss B_{OPN}= -40Gauss, B_{RPN}= -20Gauss
- Good RF noise immunity
- No need pull-up resistor
- Small Solution Size
- RoHS & Green Compliant
- DFN1014-4L, DFN1010-4L and SOT23-5L Packages
- -40°C to +125 °C Temperature Range

Applications

- Cover switch in clam-shell cellular phones
- Cover switch in Notebook, PC/PAD
- Contact-less switch in consumer products
- Solid State Switch
- Handheld Wireless Handset Awake Switch
- Lid close sensor for battery-powered devise
- Magnet proximity sensor for reed switch replacement in low duty cycle applications
- DV, DSC, and White Goods

Ordering Information

/	
Package:	Packing:
D:DFN1014-4L	R:Tape&Reel
D1:DFN1010-4L	
ST: SOT23-5L	
W: SOT553	

AS1821XXX

| Temperature Grade: N: -40°C~85°C Y: -40°C~125°C

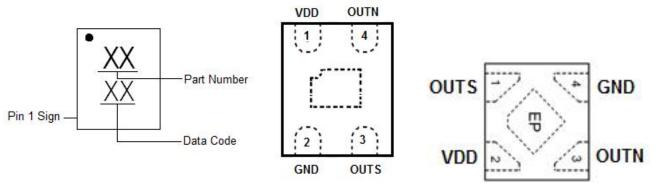
Part Number	B _{OP} (Gauss)	B _{RP} Gauss)	Package Type	Package Qty	Temperature	Eco Plan
AS1821DRN	±40Gauss	±20Gauss	DFN1014-4L	7-in reel 3000pcs/reel	-40∼85° ℃	Green
AS1821D1RN	±40Gauss	±20Gauss	DFN1010-4L	7-in reel 10000pcs/reel	-40∼85℃	Green
AS1821STRN	±40Gauss	±20Gauss	SOT23-5L	7-in reel 3000pcs/reel	-40∼85° ℃	Green
AS1821WRN	±40Gauss	±20Gauss	SOT553	7-in reel 3000pcs/reel	-40∼85° ℃	Green
AS1821DRY	±40Gauss	±20Gauss	DFN1014-4L	7-in reel 3000pcs/reel	-40∼125° ℃	Green
AS1821D1RY	±40Gauss	±20Gauss	DFN1010-4L	7-in reel 10000pcs/reel	-40∼125° ℃	Green
AS1821STRY	±40Gauss	±20Gauss	SOT23-5L	7-in reel 3000pcs/reel	-40∼125 ℃	Green
AS1821WRY	±40Gauss	±20Gauss	SOT553	7-in reel 3000pcs/reel	-40∼125° ℃	Green





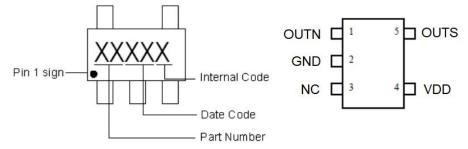
Marking & Pin Assignment

DFN1014-4L/DFN1010-4L (Top View):



Pin Name	Pin	No.	I/O	Pin Function	
FIII Naille	DFN1014-4L	DFN1010-4L	"0	Finitunction	
VDD	1	2	Р	Input Power Supply.	
GND	2	4	Р	Ground.	
OUTS	3	1	0	Output Pin for South Pole.	
OUTN	4	4 3		Output Pin for North Pole.	

SOT553/SOT23-5L:



Pin Name	Pin	No.	I/O	Pin Function
FIII Name	SOT23-5L	SOT553	1/0	Fill Function
OUTN	1	1	0	Output Pin for North Pole.
GND	2	2	P Ground	
NC	3	3	-	Not Connected
VDD	4	4	P Input Power Supply	
OUTS	5	5	O Output Pin for South Pole.	

Typical Application Circuit

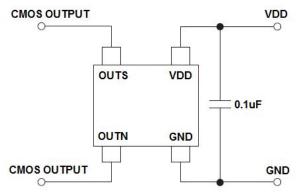


Figure 1, Typical Application Circuit of AS1821

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Block Diagram

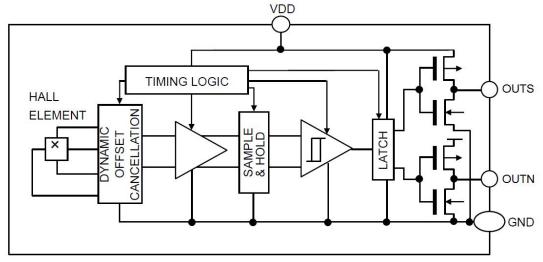


Figure 3, Block Diagram of AS1821

■ Absolute Maximum Ratings¹ (T_A=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit				
V _{DD} Pin to GND		V _{DD}	-0.3 to 5.0	V			
Output Pin to GND		VOUTPUT	-0.3 to V _{DD} +0.3	V			
Max. Continuous Output Current		Ioutmax	2.0	mA			
Magnetic Flux Density	Magnetic Flux Density		Unlimited	Gauss			
Package Power Dissipation	DFN-4L	PD	250	mW			
Storage Temperature Rang	Storage Temperature Range		-55 to +150	°C			
Operating Junction Temperature Range		T _{OP}	-40 to +150	°C			
Maximum Soldering Temperature (at I	eads, 10 sec)	T _{LEAD}	300	°C			

Recommended Operating Conditions²

Parameter	Symbol	Rating	Unit
V _{DD} Pin to GND	V _{DD}	1.65 to 5.0	V
Continuous Output Current	I _{OUT}	1.0	mA
ESD (HBM)	HBM	8000	V
Operating Temperature Range	T _{OP}	-40 to +125	°C

Note: 1: Stresses above those listed in absolute maximum ratings may cause permanent damage to the device. Functional operation at conditions other than the operating conditions specified is not implied. Only one absolute maximum rating should be applied at any one time. 2: The device is not guaranteed to function outside of its operating conditions.

Electrical Characteristics

(T_A = -40 to +125 $^{\circ}$ unless otherwise noted. Typical values are at T_A = +25 $^{\circ}$, V_{DD} = 1.8V)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{DD}	Input Voltage		1.65	1.8	5.0	V
I _{DD} (AVG)	Supply Current	Average supply current, $T_A = 25^{\circ}C$, $V_{DD} = 1.8V$	-	1.7	2.5	μA
I _{DD} (AVG)	Supply Current	Average supply current, T _A =25℃, V _{DD} =4.2V	-	2.5	4.0	μA
T _{awake}	Awake Time		-	50	100	μs
T _{period}	Period		-	100	150	ms
D.C.	Duty Cycle		-	0.05	-	%
V _{OH}	Output Off Voltage (High side)	I _{OUT} =+1mA	V _{DD} -0.3	V _{DD} -0.1	V _{DD} +0.3	V
Vol	Output On Voltage (Low side)	I _{OUT} =-1mA	-0.3	0.1	+0.3	V
Magnetic F	Para.					
BOPS	Magnetic Operating Point		-	40	50	Gauss
BOPN			-50	-40	-	
Brps	Magnetic Release Point		10	20	-	Gauss
B _{RPN}			-	-20	-10	
B _{HYS}	Hysteresis Window		-	20	-	Gauss

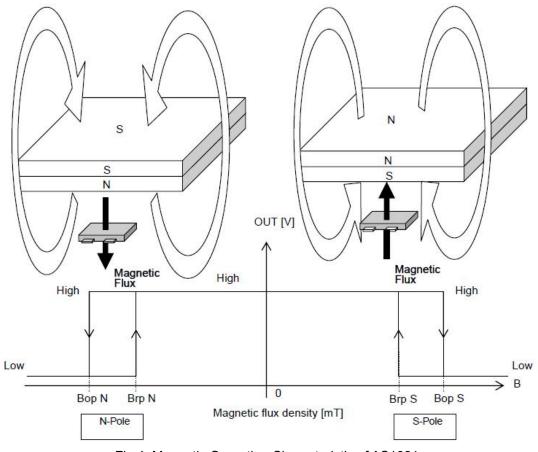
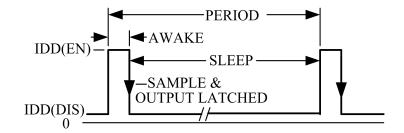


Fig 4, Magnetic Operation Characteristic of AS1821



Function Description



Micro-power Operation

Internal timing circuitry activates the sensor for 50µs and deactivates it for the remainder of the period (100ms). A short "awake" time allows for stabilization prior to the sensor sampling and data latching on the falling edge of the timing pulse. The output during the "sleep" time is latched in the last sampled state. The supply current is not affected by the output state.

Chopper-Stabilized Technique

The Hall element can be considered as a resistor array similar to a Wheatstone bridge. A large portion of the offset is a result of the mismatching of these resistors. These devices use a proprietary dynamic offset cancellation technique, with an internal high-frequency clock to reduce the residual offset voltage of the Hall element that is normally caused by device over-molding, temperature dependencies, and thermal stress. The chopper-stabilizing technique cancels the mismatching of the resistor circuit by changing the direction of the current flowing through the Hall plate using CMOS switches and Hall voltage measurement taps, while maintains the Hall voltage signal that is induced by the external magnetic flux. The signal is then captured by a sample-and-hold circuit and further processed using low-offset bipolar circuitry. This technique produces devices that have an extremely stable quiescent Hall output voltage, are immune to thermal stress, and have precise recoverability after temperature cycling. A relatively high sampling frequency is used for faster signal processing capability can be processed.

Magnetic Field Detection Mechanism

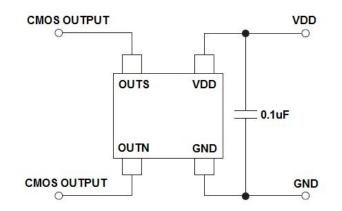
The Hall IC cannot detect magnetic fields that run horizontal to the package top layer. Be certain to configure the Hall IC so that the magnetic field is perpendicular to the top layer.

Operation

The output of this device switches low (turns on) when a magnetic field perpendicular to the Hall sensor exceeds the operate point B_{OPS} (or is less than B_{OPN}). After turn-on, the output is capable of sinking up to 1mA and the output voltage is $V_{OUT}(ON)$. When the magnetic field is reduced below the release point B_{RPS} (or increased above B_{RPN}), the device output switches high (turns off). The difference between the magnetic operates and release points are the hysteresis (Bhys) of the device. This built-in hysteresis allows clean switching of the output even in the presence of external mechanical vibration and electrical noise.



Applications:



AS1821's pole-independent sensing technique allows for operation with either a north or south poles magnet orientation, enhancing the manufacturability of the device. The state-of-the-art technology provides the same output polarity for either pole face.

C1 serves two purposes: minimizing ripples on the input voltage and enhancing immunity from RF transmission noises within close proximity. Recommended values are between 10nF and 100nF. The larger the capacitance, the better the noise immunity is for the AS1821.

It is strongly recommended that an external bypass capacitor be connected (in close proximity to the Hall sensor) between the supply and ground of the device to reduce both external noise and noise generated by the chopper-stabilization technique. This is especially true due to the relatively high impedance of battery supplies. The simplest form of magnet that will operate these devices is a bar magnet with either pole near the branded surface of the device.

Thermal Considerations

The maximum IC junction temperature should be restricted to 125°C under normal operating conditions. This restriction limits the power dissipation of the AS1821. Calculate the maximum allowable dissipation, $P_{D(max)}$, and keep the actual dissipation less than or equal to $P_{D(max)}$. The maximum-power-dissipation limit is determined using following equation:

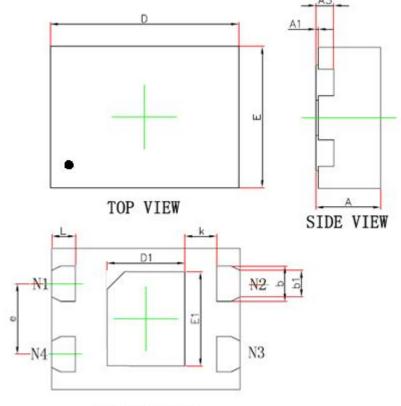
$$P_{D(MAX)} = \frac{125^{\circ}\mathrm{C} - T_{A}}{R_{\theta IA}}$$

Where, TA is the maximum ambient temperature for the application. R $_{\theta}$ JA is the thermal resistance junction-to-ambient given in Power Dissipation Table.



Package Information

DFN1014-4L:

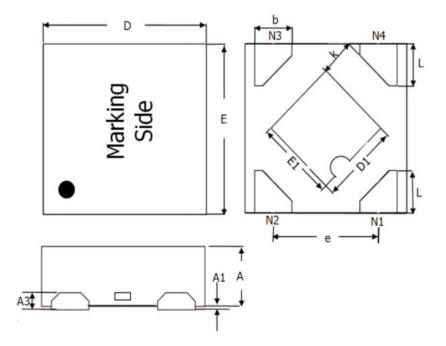


BOTTOM VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min.	Nom.	Max.	Min.	Nom.	Max.
А	0. 320	0.370	0.400	0.013	0.014	0.016
A1	0.000	-	0.050	0.000	-	0.002
A3		0.102 (BSC)			0.004 (BSC	;)
D	1.300	1.400	1.500	0.051	0.055	0.059
E	0.900	1.000	1.100	0.035	0.039	0.043
D1	0.500	0.600	0.700	0.020	0.024	0.028
E1	0.700	0.800	0.900	0.028	0.031	0.035
L	0.150	0.200	0.250	0.006	0.008	0.010
b	0.170	0.220	0.270	0.007	0.009	0.011
b1	0.170	0.220	0.270	0.007	0.009	0.011
е	0.500 (BSC)			0.020 (BSC)		
k		0.200 (BSC)			0.008 (BSC	;)



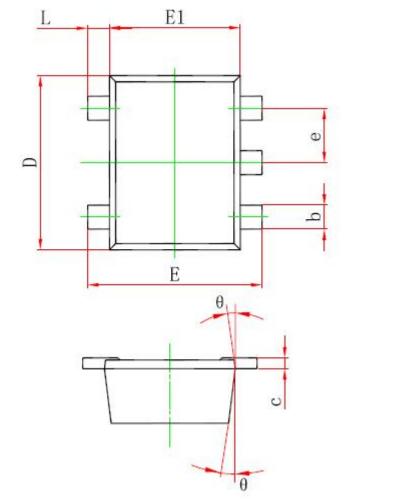
DFN1010-4L:

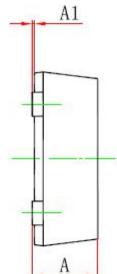


Sumbol	Dimensions In	Dimensions In Millimeters		In Inches
Symbol	Min.	Max.	Min.	Max.
A	0.340	0.400	0.014	0.016
A1	0.000	0.050	0.000	0.002
A3	0.152 E	BSC	0.006	BSC
D	0.950	1.050	0.038	0.042
E	0.950	1.050	0.038	0.042
D1	0.450	0.550	0.018	0.022
E1	0.450	0.550	0.018	0.022
k	0.211 E	211 BSC 0.008 BSC		BSC
b	0.180	0.280	0.0072	0.0112
е	0.625 BSC		0.025 BSC	
L	0.200	0.300	0.008	0.012

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SOT553:

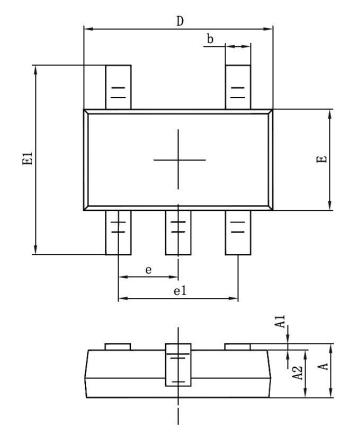


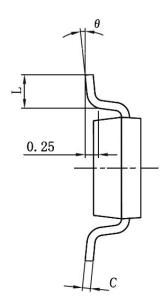


Symbol	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.525	0.600	0.021	0.024	
A1	0.000	0.050	0.000	0.002	
е	0.450	0.550	0.018	0.022	
с	0.090	0.160	0.004	0.006	
D	1.500	1.700	0.059	0.067	
b	0.170	0.270	0.007	0.011	
E1	1.100	1.300	0.043	0.051	
E	1.500	1.700	0.059	0.067	
θ	7° R	7° REF		REF	
L	0.100	0.300	0.004	0.012	



SOT23-5L:

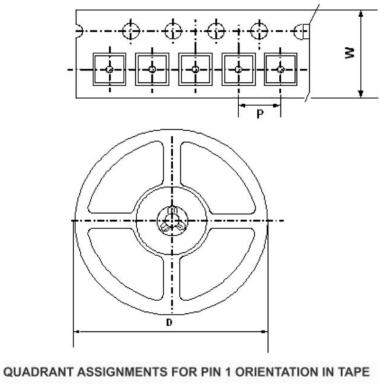


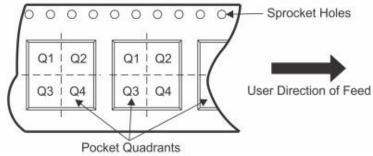


Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	0.900	1.450	0.036	0.058	
A1	0.000	0.150	0.000	0.006	
A2	0.900	1.300	0.036	0.052	
b	0.300	0.500	0.012	0.020	
С	0.080	0.200	0.003	0,008	
D	2.800	3.000	0.112	0.120	
E	1.500	1.700	0.060	0.068	
E1	2.600	3.000	0.104	0.120	
е	0.95(BSC)	0.037(BSC)		
e1	1.90(BSC)		0.075(BSC)		
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



Packing Information





Device	Package Type	SPQ	Carrier Width (W)	Pitch(P)	Reel Size(D)	Pin1 Quadrant
AS1821DRN/Y	DFN1014-4L	3000pcs	8.0±0.1 mm	4.0±0.1 mm	180±1 mm	Q2
AS1821D1RN/Y	DFN1010-4L	10000pcs	8.0±0.1 mm	4.0±0.1 mm	180±1 mm	Q1
AS1821STRN/Y	SOT23-5L	3000pcs	8.0±0.1 mm	4.0±0.1 mm	180±1 mm	Q3
AS1821WRN/Y	SOT553	3000pcs	8.0±0.1 mm	4.0±0.1 mm	180±1 mm	Q3

*All dimensions are nominal